

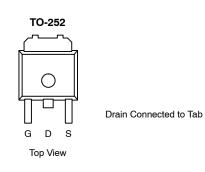
2SK3405-Z-VB Datasheet

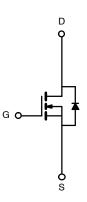
N-Channel 20-V (D-S)175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a		
20	0.0045 @ V _{GS} = 4.5 V	100		
20	0.006 @ V _{GS} = 2.5 V	90		

FEATURES

- Trench Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R_g Tested





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	20			
Gate-Source Voltage		V _{GS}	±15	V		
	$T_{C} = 25^{\circ}C$		100			
Continuous Drain Current ^a	$T_{C} = 100^{\circ}C$	- I _D	80			
Pulsed Drain Current		I _{DM}	200	— A		
Continuous Source Current (Diode Conduction) ^a		IS	65			
	$T_{C} = 25^{\circ}C$	_	71			
Maximum Power Dissipation	T _A = 25°C	P _D	8.3 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
	$t \le 10$ sec.		15	18	°C/W		
Maximum Junction-to-Ambient ^b	Steady State	R _{thJA}	40	50			
Maximum Junction-to-Case		R _{thJC}	1.75	2.1			

Notes

a. Package Limited

b. Surface Mounted on 1" x 1" FR4 Board

 $\text{c.} \quad t \, \leq \, 10 \, \, \text{sec}$

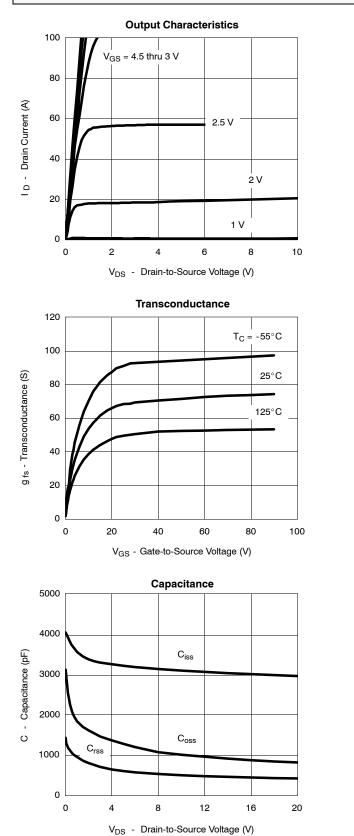
Parameter	Symbol	Test Condition Min		Тур ^а	Max	Unit	
Static			1				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 250 μ A	20			v	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\;\mu A$	0.5		1.5		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
	1 . I	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μΑ	
Zero Gate Voltage Drain Current	IDSS	V_{DS} = 20 V, V_{GS} = 0 V, T_J = 125 $^\circ C$			50		
On-State Drain Current ^b	I _{D(on)}	V_{DS} = 5 V, V_{GS} = 4.5 V	100			Α	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0045		Ω	
Drain-Source On-State Resistance ^b	r _{DS(on)}	V_{GS} = 4.5 V, I _D = 20 A, T _J = 125°C		0.0055			
		$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.006		1	
Forward Transconductanceb	9fs	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 40 \text{ A}$	20			S	
Dynamic ^a							
Input Capacitance	C _{iss}			3660		pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz		730			
Reverse Transfer Capacitance	C _{rss}			375			
Total Gate Charge ^c	Qg			26	35	nC	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 10 V, $~V_{GS}$ = 4.5 V, I_{D} = 40 A		5			
Gate-Drain Charge ^c	Q _{gd}			7		1	
Gate Resistance	Rg	1			3.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			20	35	- ns	
Rise Time ^c	t _r	V_{DD} = 10 V, R_L = 0.25 Ω		120	190		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 40$ Å, $V_{GEN} = 4.5$ V, $R_G = 2.5 \Omega$		45	70		
Fall Time ^c	t _f			20	35		
Source-Drain Diode Ratings an	d Characteristi	c (T _C = 25°C)					
Pulsed Current	I _{SM}				100	А	
Diode Forward Voltage ^b	V _{SD}	I_F = 100 A, V_{GS} = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 40 A, di/dt = 100 A/μs 35 7		70	ns		

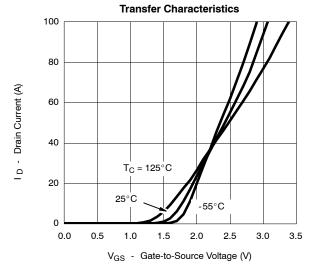
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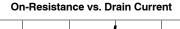
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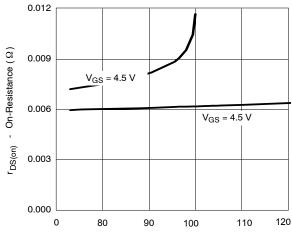


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

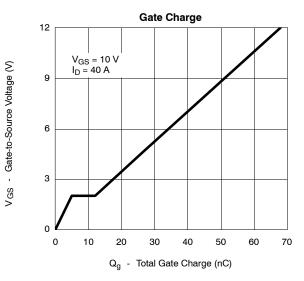




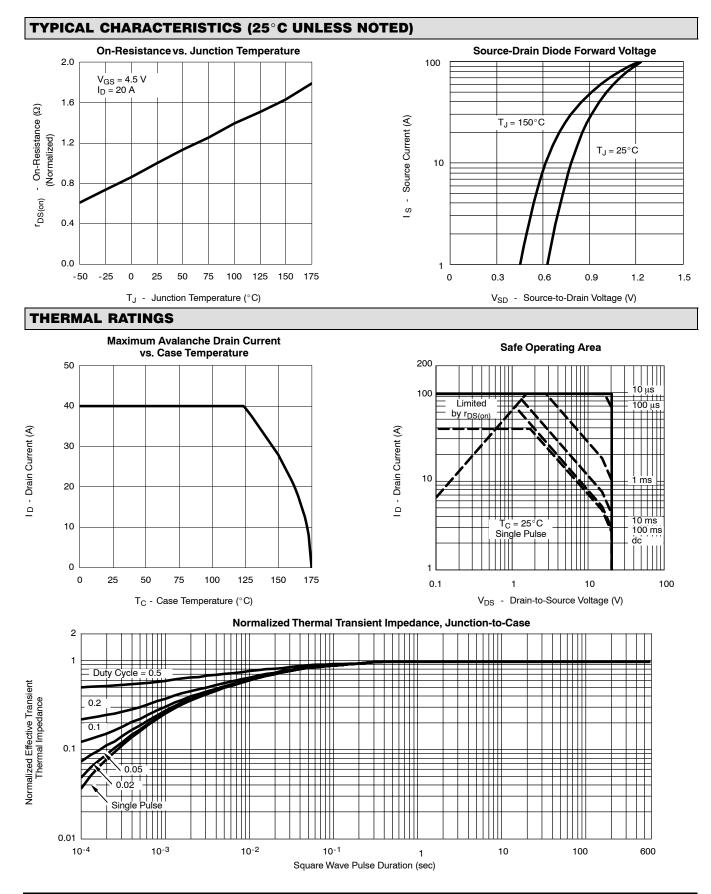




I_D - Drain Current (A)

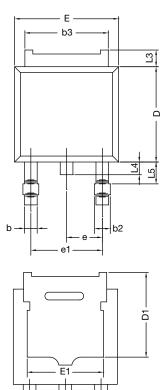


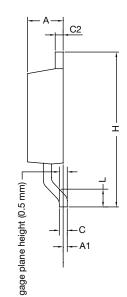






TO-252AA CASE OUTLINE





	MILLIN	IETERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
А	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC	0.090 BSC			
e1	4.56 BSC		0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12- DWG: 534	0247-Rev. M, 7	24-Dec-12				

Note

• Dimension L3 is for reference only.



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